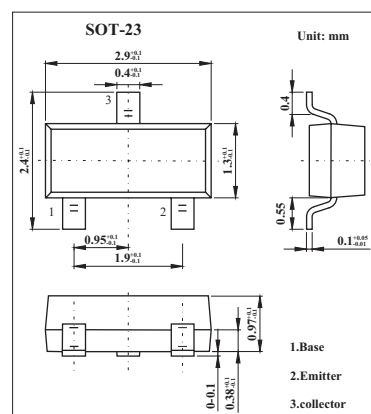


Silicon PNP Epitaxial Planar Type

2SB970

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$.
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-15	V
Collector-emitter voltage	V_{CEO}	-10	V
Emitter-base voltage	V_{EBO}	-7	V
Collector current	I_C	-5	A
Peak collector current	I_{CP}	-1	A
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	$I_C = -10 \mu\text{A}$, $I_E = 0$	-15			V
Collector-emitter voltage	V_{CEO}	$I_C = -1 \text{ mA}$, $I_B = 0$	-10			V
Emitter-base voltage	V_{EBO}	$I_E = -10 \mu\text{A}$, $I_C = 0$	-7			V
Collector-base cutoff current	I_{CBO}	$V_{CB} = -10 \text{ V}$, $I_E = 0$			-100	nA
Forward current transfer ratio	h_{FE}	$V_{CE} = -2 \text{ V}$, $I_C = -0.5 \text{ A}$	130		350	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -0.4 \text{ A}$, $I_B = -8 \text{ mA}$		-0.16	-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -0.4 \text{ A}$, $I_B = -8 \text{ mA}$		-0.8	-1.2	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}$, $I_E = 50 \text{ mA}$, $f = 200 \text{ MHz}$		130		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}$, $I_E = 0$, $f = 1.0 \text{ MHz}$		22		pF

* Pulse measurement.

■ h_{FE} Classification

Marking	1R	
Rank	R	S
h_{FE}	130~220	180~350